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Seat	
No.	

[4956]-102

F.E. EXAMINATION, 2016

ENGINEERING PHYSICS

(2012 **PATTERN**)

Time: Two Hours

Maximum Marks: 50

N.B. :— (i) Neat diagrams must be drawn wherever necessary.

- (ii) Figures to the right indicate full marks.
- (iii) Use of logarithmic tables, slide rule, Mollier charts, electronic pocket calculator and steam tables is allowed.
- (iv) Assume suitable data, if necessary.
- (v) All questions are compulsory.

Constants :— (i) Mass of electron = m_e = 9.1 × 10⁻³¹ kg

- (ii) Charge on electron = $e = 1.9 \times 10^{-19}$ C
- (iii) Mass of proton = $m_p = 1.673 \times 10^{-27} \text{ kg}$
- (iv) Mass of neurton = $m_n = 1.675 \times 10^{-27} \text{ kg}$
- (v) Planck's constant = $h = 6.63 \times 10^{-34}$ J.s.
- (vi) Velocity of light = $c = 3 \times 10^8$ m/s
- 1. (a) For a plane diffraction grating, starting from the equations of resultant amplitude and intensity, derive conditions for maxima and minima of the diffraction pattern. [6]

<i>(b)</i>	Explain	how	ultrasonic	waves	are	used	for	detection	of	flaws
	in meta	ıl.								[3]

(c) A hall of dimensions 20 m × 20 m × 20 m has a reverberation time of 1.2 sec. Find average absorption coefficient. [3]

Or

- **2.** (a) What is magnetostriction effect? Explain construction and working of magnetostriction oscillator. [6]
 - (b) Explain with suitable diagram how interference is used to design anti-reflection coating. [3]
 - (c) A parallel beam of light 622 nm incident on a glass plate of refractive index 1.5 such that angle of refraction into the plate is 60°. Calculate the smallest thickness of the plate which will appear dark by reflection. [3]
- 3. (a) What is double refraction? Explain this phenomenon on the basis of Huygen's theory. [6]
 - (b) What is Fermi energy in semiconductor? With the help of labeled diagram show the position of Fermi level in the case of a diode that is connected in forward bias. [3]
 - (c) Calculate the number of acceptor atoms that need to be doped in germanium sample to obtain the resistivity of 8 Ω cm. [Given: mobility $\mu = 1600$ cm²/V.s] [3]

4.	(a)	Derive an expression for conductivity in case of intrinsic a	and				
		extrinsic semiconductors.	[6]				
	(<i>b</i>)	What is stimulated emission of radiations? Explain	its				
		significance in production of laser.	[3]				
	(c)	Explain any one engineering application of laser.	[3]				
5.	(a)	Deduce Schrödinger's time independent wave equation.	[6]				
	(<i>b</i>)	State and explain Heisenberg's uncertainty principle.	[4]				
	(c)	Calculate de Broglie wavelength for a proton moving with veloc	city				
		1 percent of velocity of light.	[3]				
		Or					
6. (a)	Define phase velocity and group velocity. Show that group						
		velocity is equal to particle velocity.	[6]				
	(<i>b</i>)	Explain why probability of finding of a particle cannot	be				
		predicted by the interpretation of wave function ψ . Expl	ain				
		physical significance of $ \psi ^2$.	[4]				
	(c)	A neutron is trapped in an infinite potential well of wie	dth				
		10^{-14} m. Calculate its first energy eigenvalue in eV.	[3]				
7.	(a)	Explain BCS theory of superconductivity. Mention why sup	oer-				
		conductivity is observed below critical temperature.	[6]				
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- (b) Explain any one method for synthesis of nano-particles. [4]
- (c) Explain the applications of nano-particles in the field of automobiles. [3]

Or

- 8. (a) Why are the properties of nano-particles different from that of the bulk materials? Explain any two properties of nanoparticles. [6]
 - (b) Explain in brief: [4]
 - (i) Meissner effect
 - (ii) Critical magnetic field.
 - (c) Explain the applications of superconductors in the field of electronics. [3]